Supplementary Information

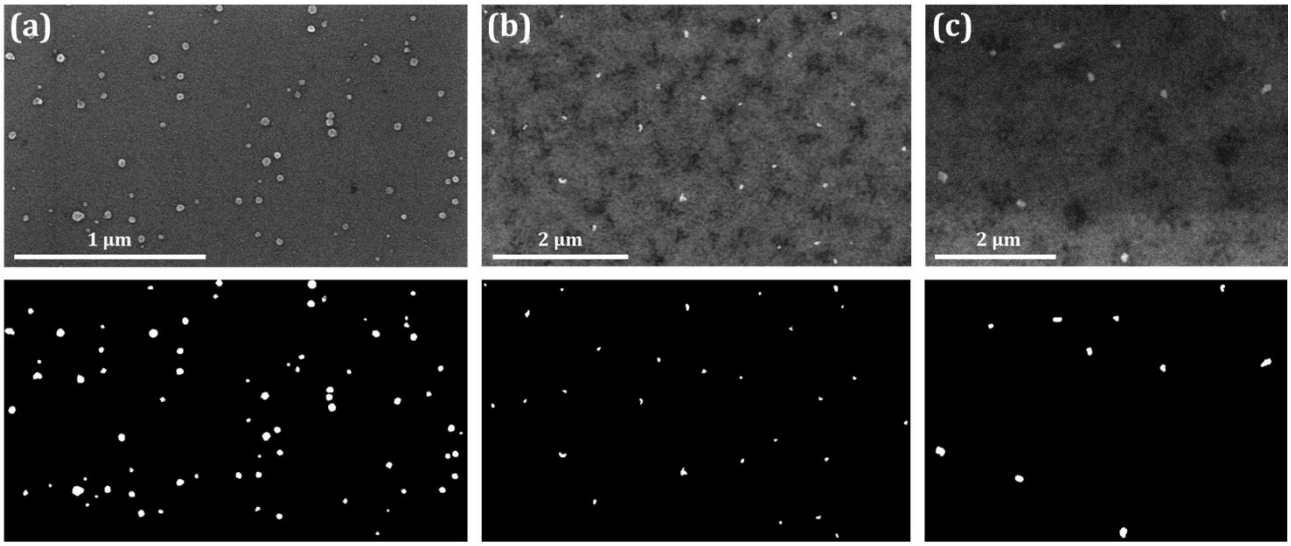

Figure S1. FESEM images and their high contrast counterparts of SiO_x NPs synthesized at voltages of (a) 7.5 V, (b) 10.0 V, and (c) 12.5 V at a constant temperature of 5 °C.

Table S1. Wt% of the elements in SiO_x NPs synthesized at voltages of (a) 7.5 V, (b) 10.0 V, and (c) 12.5 V at a constant temperature of 5 °C.

Anodization voltage (V)	Si (wt%)	O (wt%)
7.5	71.5	28.5
10.0	64.1	35.9
12.5	59.2	40.8